

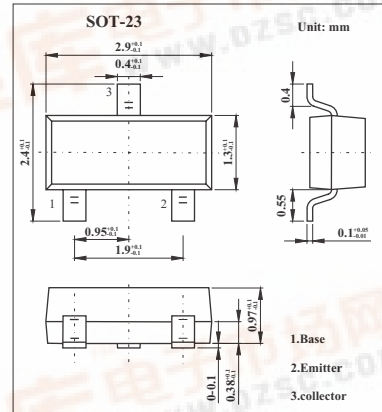
SMD Type Transistors

Silicon NPN Epitaxial

2SC2463

Features

- Low frequency amplifier.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	55	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>C</sub>	100	mA
Collector dissipation	P <sub>C</sub>	150	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	55			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	5			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0			0.5	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 2V, I <sub>C</sub> = 0			0.5	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 12V, I <sub>C</sub> = 2mA	250		1200	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA			0.5	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 12V, I <sub>C</sub> = 2mA			0.75	V

hFE Classification

Marking	DD	DE	DF
hFE	250~500	400~800	600~1200

